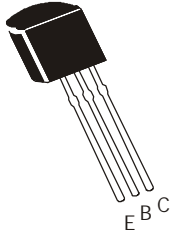


PNP SILICON PLANAR EPITAXIAL TRANSISTORS

CP756 / CP757



TO-92 Plastic Package

Medium Power Transistors are Designed for Applications Requiring High Breakdown Voltage and Low Saturation Voltage

Complementary CN656 and CN657

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

DESCRIPTION	SYMBOL	CP756	CP757	UNIT
Collector Base Voltage	V_{CBO}	200	300	V
Collector Emitter Voltage	V_{CEO}	200	300	V
Emitter Base Voltage	V_{EBO}	5		V
Peak Pulse Current	$*I_{CM}$	1.0		A
Collector Current Continuous	I_C	0.5		A
Power Dissipation at $T_a=25^\circ\text{C}$	P_D	0.9		W
Derate Above 25°C		7.2		mW/ $^\circ\text{C}$
Power Dissipation at $T_a=25^\circ\text{C}$	$**P_D$	1.1		W
Power Dissipation at $T_c=25^\circ\text{C}$	P_D	2.2		W
Operating and Storage Junction Temperature Range	T_j, T_{stg}	- 65 to +150		$^\circ\text{C}$

Thermal Resistance

Junction to Ambient	$R_{th(j-a) 1}$	138.8	$^\circ\text{C/W}$
Junction to Ambient	$R_{th(j-a) 2+}$	113.6	$^\circ\text{C/W}$
Junction to Case	$R_{th(j-c)}$	56.8	$^\circ\text{C/W}$

* Consult safe operating area graph for conditions.

**Transistors mounted on printed circuit board. Lead Length 4mm, mounting pad for collector lead min 10mm x 10 mm, copper

2+ Device mounted on P.C.B with copper equal to 1sq.inch. Minimum

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless specified otherwise)

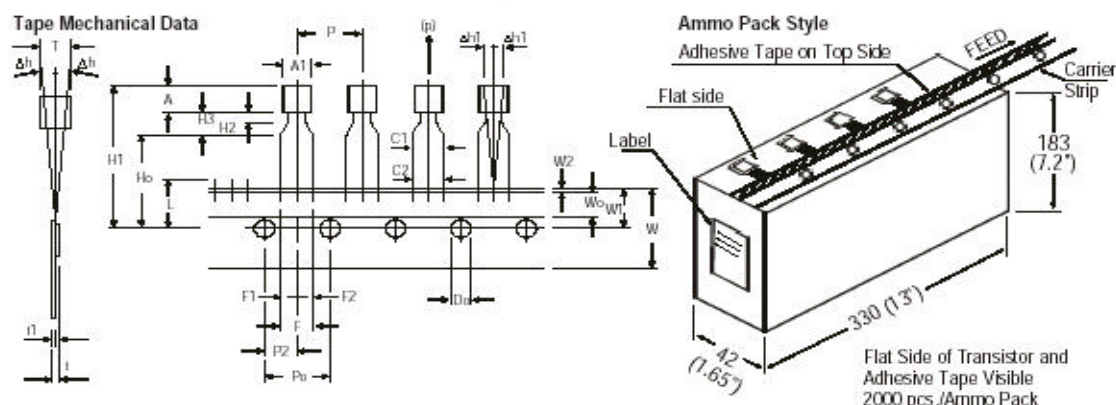
DESCRIPTION	SYMBOL	TEST CONDITION	MIN	MAX	UNIT
Collector Base Voltage	V_{CBO}	$I_C=100\mu\text{A}, I_E=0$	CP756 200 CP757 300		V
Collector Emitter Voltage	V_{CEO}	$I_C=1\text{mA}, I_B=0$	CP756 200 CP757 300		V
Emitter Base Voltage	V_{EBO}	$I_E=100\mu\text{A}, I_C=0$	5.0		V
Collector Cut Off Current	I_{CBO}	$V_{CB}=160\text{V}, I_E=0$ $V_{CB}=200\text{V}, I_E=0$	CP756 CP757	100 100	nA
Emitter Cut Off Current	I_{EBO}	$V_{EB}=3\text{V}, I_C=0$		100	nA
Collector Emitter Saturation Voltage	$*** V_{CE(sat)}$	$I_C=100\text{mA}, I_B=10\text{mA}$		0.5	V
Base Emitter Saturation Voltage	$*** V_{BE(sat)}$	$I_C=100\text{mA}, I_B=10\text{mA}$		1.0	V
Base Emitter On Voltage	$*** V_{BE(on)}$	$I_C=100\text{mA}, V_{CE}=5\text{V}$		1.0	V
DC Current Gain	$*** h_{FE}$	$I_C=100\text{mA}, V_{CE}=5\text{V}$ $I_C=10\text{mA}, V_{CE}=5\text{V}$	50 40		
Transition Frequency	f_T	$I_C=10\text{mA}, V_{CE}=20\text{V}, f=20\text{MHz}$	30		MHz
Output Capacitance	C_{obo}	$V_{CB}=20\text{V}, I_E=0, f=1\text{MHz}$		20	pF

***Pulse conditions. Pulse Width=300ms. Duty Cycle \leq 2%

CP756_757Rev_2 120406E

TO-92 Plastic Package

TO-92 Tape and Ammo Pack



All dimensions are in mm

ITEM	SYMBOL	SPECIFICATION			
		MIN.	NOM.	MAX.	TOL.
BODY WIDTH	A1	4.45		5.20	
BODY HEIGHT	A	4.32		5.33	
BODY THICKNESS	T	3.18		4.19	
PITCH OF COMPONENT	P		12.7		± 1.0
*1 FEED HOLE PITCH	Po		12.7		± 0.3
*2 FEED HOLE CENTRE TO COMPONENT CENTRE	P2		6.35		± 0.4
DISTANCE BETWEEN OUTER LEADS	F		5.08		+ 0.6 - 0.2
*3 COMPONENT ALIGNMENT SIDE VIEW	Δh		0	1.0	
*4 COMPONENT ALIGNMENT FRONT VIEW	Δh1		0	1.3	
TAPE WIDTH	W		18		± 0.5
HOLD-DOWN TAPE WIDTH	Wo		6		± 0.2
HOLE POSITION	W1		9		+ 0.7 - 0.5
HOLD-DOWN TAPE POSITION	W2	0.0		0.7	
LEAD WIRE CLINCH HEIGHT	Ho		16		± 0.5
COMPONENT HEIGHT	H1			24.0	
LENGTH OF SNIPPED LEADS	L			11.0	
FEED HOLE DIAMETER	Do		4		± 0.2
*5 TOTAL TAPE THICKNESS	t			1.2	
LEAD - TO - LEAD DISTANCE	F1, F2	2.40		2.70	- 0.1
STAND OFF	H2	0.45		1.45	
CLINCH HEIGHT	H3			3.0	
LEAD PARALLELISM	C1 - C2			0.22	
PULL - OUT FORCE	(p)		6N		

NOTES

- Maximum alignment deviation between leads will not be greater than 0.2mm.
- Maximum non-cumulative variation between tape feed holes shall not exceed 1 mm in 20 pitches.
- Holddown tape will not exceed beyond the edge(s) of carrier tape and there shall be no exposure of adhesive.
- There will be no more than three (3) consecutive missing components in a tape.
- A tape trailer, having at least three feed holes are provided after the last component in a tape.
- Splices should not interfere with the sprocket feed holes.

REMARKS

- *1 Cumulative pitch error 1.0 mm/20 pitch
- *2 To be measured at bottom of clinch
- *3 At top of body
- *4 At top of body
- *5 t1 0.3 – 0.6 mm

CP756_757Rev_2 120406E

Component Disposal Instructions

1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

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